

# Nunes, Luis C

## List of Publications by Year in descending order

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40  
papers

481  
citations

933264

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h-index

887953

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all docs

40  
docs citations

40  
times ranked

349  
citing authors

#	ARTICLE	IF	CITATIONS
1	Quasi-Load Insensitive Doherty PA Using Supply Voltage and Input Excitation Adaptation. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 779-789.	2.9	11
2	The Impact of Long-Term Memory Effects on the Linearizability of GaN HEMT-Based Power Amplifiers. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 1377-1390.	2.9	10
3	Output Impedance Profile Selection in Sequential LMBAs using an Automatic Method. , 2022, , .		4
4	Characterization, Modeling, and Compensation of the Dynamic Self-Biasing Behavior of GaN HEMT-Based Power Amplifiers. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 529-540.	2.9	10
5	Dynamic Supply Voltage Control for PA Output Power Correction Under Variable Loading Scenarios. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 745-755.	2.9	12
6	New Transistor Behavioral Model Formulation Suitable for Doherty PA Design. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 2138-2147.	2.9	12
7	Automatic Methodology for Wideband Power Amplifier Design. IEEE Microwave and Wireless Components Letters, 2021, 31, 989-992.	2.0	6
8	A Compact Impedance Measurement Solution for Systems Operating in Load Varying Scenarios. IEEE Access, 2021, 9, 38757-38766.	2.6	4
9	Optimal Supply Voltage for PA Output Power Correction under Load Varying Scenarios. , 2020, , .		3
10	A Transient Two-Tone RF Method for the Characterization of Electron Trapping Capture and Emission Dynamics in GaN HEMTs. , 2020, , .		3
11	Explaining the Different Time Constants Extracted from Low Frequency $Y_{22}$ and $S_{DS}$ -DLTS on GaN HEMTs. , 2020, , .		6
12	Transient Pulsed S-Parameters for Trapping Characterization. , 2020, , .		5
13	Impact of the Input Baseband Impedance on the Instantaneous Bandwidth of Wideband Power Amplifiers. , 2019, , .		2
14	An Accurate Characterization of Capture Time Constants in GaN HEMTs. IEEE Transactions on Microwave Theory and Techniques, 2019, 67, 2465-2474.	2.9	36
15	Impact of the Input Baseband Terminations on the Efficiency of Wideband Power Amplifiers Under Concurrent Band Operation. IEEE Transactions on Microwave Theory and Techniques, 2019, 67, 5127-5138.	2.9	10
16	Memristive Properties of GaN HEMTs Containing Deep-Level Traps. Physica Status Solidi (B): Basic Research, 2019, 256, 1800387.	0.7	4
17	Efficiency Degradation Analysis in Wideband Power Amplifiers. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 5640-5651.	2.9	14
18	Pulsed $I$ and $V$ and $S$ -parameters measurement system for isodynamic characterization of power GaN HEMT transistors. International Journal of RF and Microwave Computer-Aided Engineering, 2018, 28, e21515.	0.8	15

#	ARTICLE	IF	CITATIONS
19	Efficiency Degradation in Wideband Power Amplifiers. , 2018, , .		1
20	Deep-Level Trapsâ€™ Capture Time Constant and its Impact on Nonlinear GaN HEMT Modeling. , 2018, , .		4
21	A Simple Method to Extract Trapping Time Constants of GaN HEMTs. , 2018, , .		14
22	Trapping behavior of GaN HEMTs and its implications on class B PA bias point selection. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2017, 30, e2128.	1.2	4
23	Compensation of Long-Term Memory Effects on GaN HEMT-Based Power Amplifiers. IEEE Transactions on Microwave Theory and Techniques, 2017, 65, 3379-3388.	2.9	44
24	Conservative current and charge data extracted from pulsed S-parameter measurements for GaN HEMT PA design. , 2017, , .		5
25	AM/PM distortion physical origins in Si LDMOS Doherty power amplifiers. , 2016, , .		3
26	A new nonlinear model extraction methodology for GaN HEMTs subject to trapping effects. , 2015, , .		19
27	Impact of trapping effects on GaN HEMT based Doherty PA load-pull ratios. , 2015, , .		6
28	A Simple Method to Estimate the Output Power and Efficiency Loadâ€™Pull Contours of Class-B Power Amplifiers. IEEE Transactions on Microwave Theory and Techniques, 2015, 63, 1239-1249.	2.9	44
29	Accurate Linearization with Low-Complexity Models Using Cascaded Digital Predistortion Systems. IEEE Microwave Magazine, 2015, 16, 94-103.	0.7	8
30	Soft compression and the origins of nonlinear behavior of GaN HEMTs. , 2014, , .		17
31	Efficiency dependence on the load-pull ratio of a Doherty PA. , 2014, , .		2
32	AM/AM and AM/PM Distortion Generation Mechanisms in Si LDMOS and GaN HEMT Based RF Power Amplifiers. IEEE Transactions on Microwave Theory and Techniques, 2014, 62, 799-809.	2.9	81
33	Characterizing power amplifier static AM/PM with spectrum analyzer measurements. , 2014, , .		9
34	Study of the GaN HEMT Doherty Power Amplifier distortion. , 2014, , .		4
35	AM/PM distortion in GaN Doherty power amplifiers. , 2014, , .		20
36	A single-ended power amplifier behavioral model for AM/AM and AM/PM predictions. , 2014, , .		1

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37	Soft compression and the origins of nonlinear behavior of GaN HEMTs. , 2014, , .		6
38	A new large-signal intermodulation and spurious analysis tool. , 2013, , .		5
39	A physical model of power amplifiers AM/AM and AM/PM distortions and their internal relationship. , 2013, , .		17
40	Nonlinear Microwave CAD Tools in a Power Amplifier Design Example. , 0, , 301-336.		0